

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

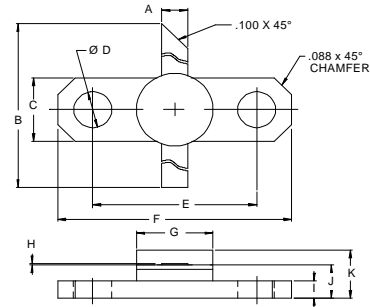
The **ASI AVD035F** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|-------------------------|-------------------|
| I_C | 2.5 A PEAK |
| V_{CB} | 55 V |
| P_{DISS} | 100 W PEAK |
| T_J | -65 °C to +200 °C |
| T_{STG} | -65 °C to +150 °C |
| θ_{JC} | 1.0 °C/W |

PACKAGE STYLE .250 2L FLG (B)


| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | .095 / 2.41 | .105 / 2.67 |
| B | 1.050 / 26.67 | |
| C | .245 / 6.22 | .255 / 6.48 |
| D | .120 / 3.05 | .140 / 3.56 |
| E | .552 / 14.02 | .572 / 14.53 |
| F | .790 / 20.07 | .810 / 20.57 |
| G | | .285 / 7.24 |
| H | .003 / 0.08 | .007 / 0.18 |
| I | .052 / 1.32 | .072 / 1.83 |
| J | .120 / 3.05 | .130 / 3.30 |
| K | | .210 / 5.33 |

ORDER CODE: ASI10558
CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-------------------------|--|---------|---------|---------|-------|
| BV_{CBO} | I _C = 10 mA | 65 | | | V |
| BV_{CER} | I _C = 10 mA R _{BE} = 10 Ω | 65 | | | V |
| BV_{EBO} | I _E = 1 mA | 3.5 | | | V |
| I_{CES} | V _{CE} = 50 V | | | 5.0 | mA |
| h_{FE} | V _{CE} = 5.0 V I _C = 500 mA | 15 | | 120 | --- |
| P_G | V _{CC} = 50 V P _{OUT} = 35 W f = 1025 - 1150 | 10 | | | dB |
| η_C | MHZ | 35 | | | % |